1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - · Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - Improved reliability, with reduced R_{th} and R_{DSon}
 - Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- · Motors, lamps and solenoid control
- · Start-Stop micro-hybrid applications
- · Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V	
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	120	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	115	W	
Static characteristics								
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		2	2.9	3.5	mΩ	



Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Dynamic chara	Dynamic characteristics								
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V; Fig. 13; Fig. 14		-	6	15	nC		
Source-drain d	liode								
Q _r	recovered charge	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; Fig. 17$		-	16	-	nC		
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C		-	0.8	-			

^{[1] 120}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	
2	S	source		D
3	S	source	a	
4	G	gate		G_(□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage						
	Name	Description	Version					
BUK7Y3R5-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	<u>SOT669</u>					

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7Y3R5-40H	73н540

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V_{GS}	gate-source voltage		[1]	-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	115	W

Symbol	Parameter	Conditions		Min	Max	Unit
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[2]	-	120	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[2]	-	93	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	526	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain d	iode					
Is	source current	T _{mb} = 25 °C	[2]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$		-	526	А
Avalanche rugo	gedness		•	·		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 120 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3] [4]	-	45	mJ

- 1] Refer to application note AN90001 for further information.
- [2] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

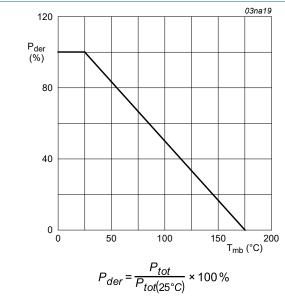
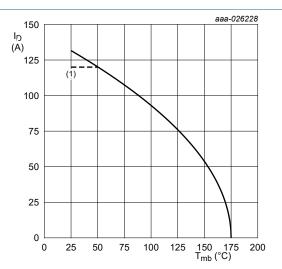


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



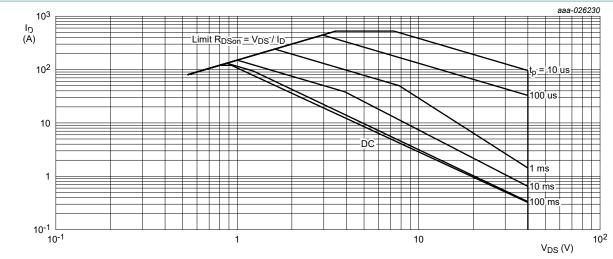
V_{GS} ≥ 10 V

(1) 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

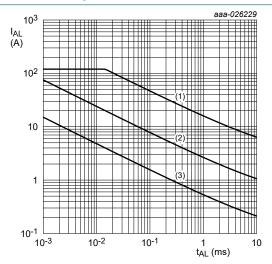
Nexperia BUK7Y3R5-40H

N-channel 40 V, 3.5 m Ω standard level MOSFET in LFPAK56



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



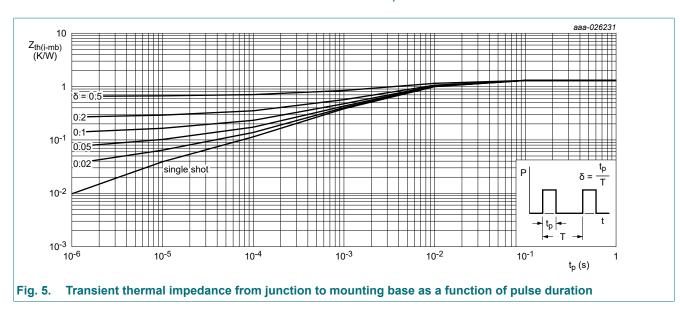
(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	1.18	1.3	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					<u> </u>
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	42.7	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 ^{\circ}C$	-	40.1	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	39.7	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-	-	4.3	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.03	1	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	1	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	37	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11	2	2.9	3.5	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 105 °C; Fig. 12	2.7	4.1	5.2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 12	2.9	4.5	5.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12	3.4	5.4	6.7	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.32	0.8	2	Ω
Dynamic ch	naracteristics		'			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V;	-	31	53	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	10	15	nC
Q _{GD}	gate-drain charge	1	-	6	15	nC

Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-		2294	3441	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-		682	954	pF
C _{rss}	reverse transfer capacitance		-		112	247	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-		10	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-		8	-	ns
t _{d(off)}	turn-off delay time		-		19	-	ns
t _f	fall time		-		9	-	ns
Source-dra	in diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-		8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-		25	-	ns
Q _r	recovered charge	V _{DS} = 20 V; <u>Fig. 17</u>	-		16	-	nC
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C	-		0.8	-	
		I_S = 25 A; dI_S/dt = -500 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; Fig. 17	-		0.6	-	

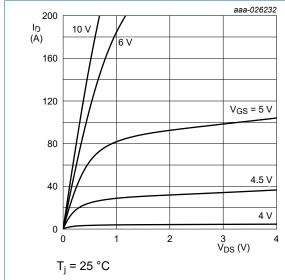


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

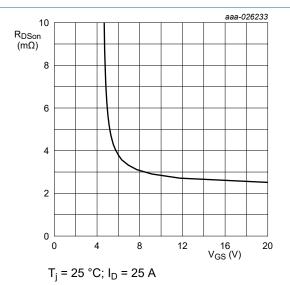


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

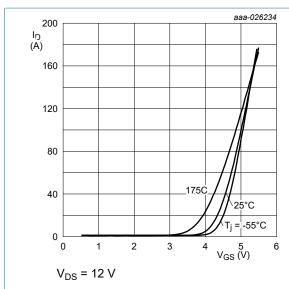


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

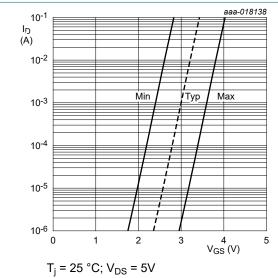


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

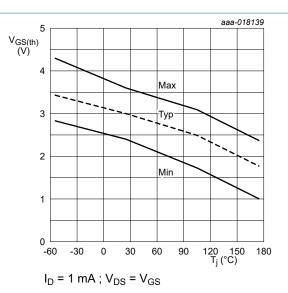


Fig. 9. Gate-source threshold voltage as a function of junction temperature

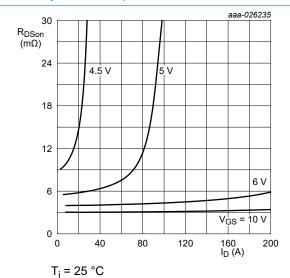


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

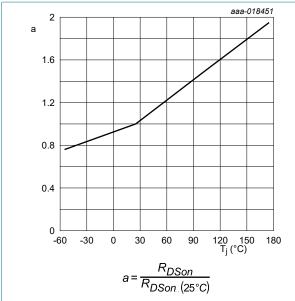


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

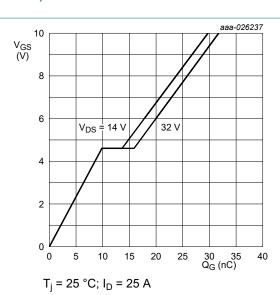


Fig. 13. Gate-source voltage as a function of gate charge; typical values

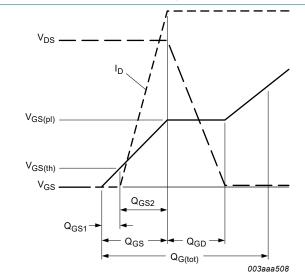


Fig. 14. Gate charge waveform definitions

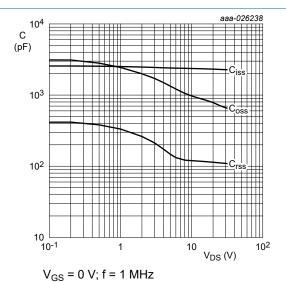


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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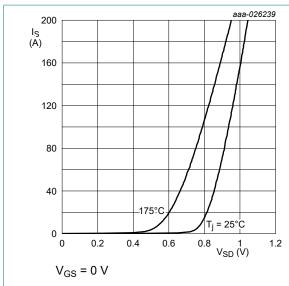


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

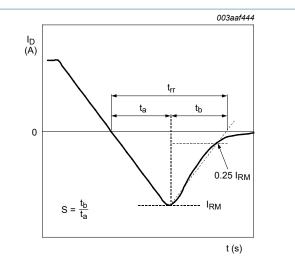
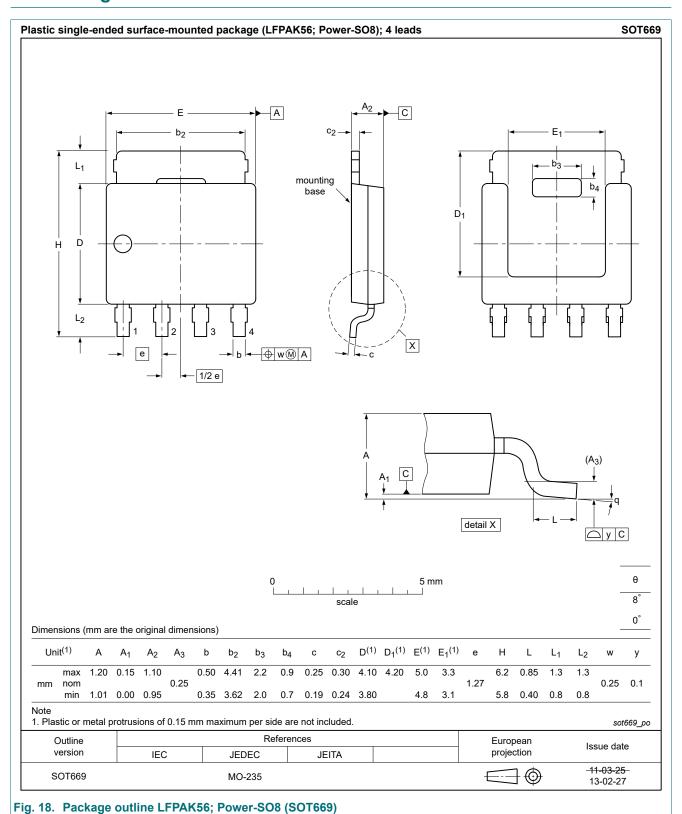
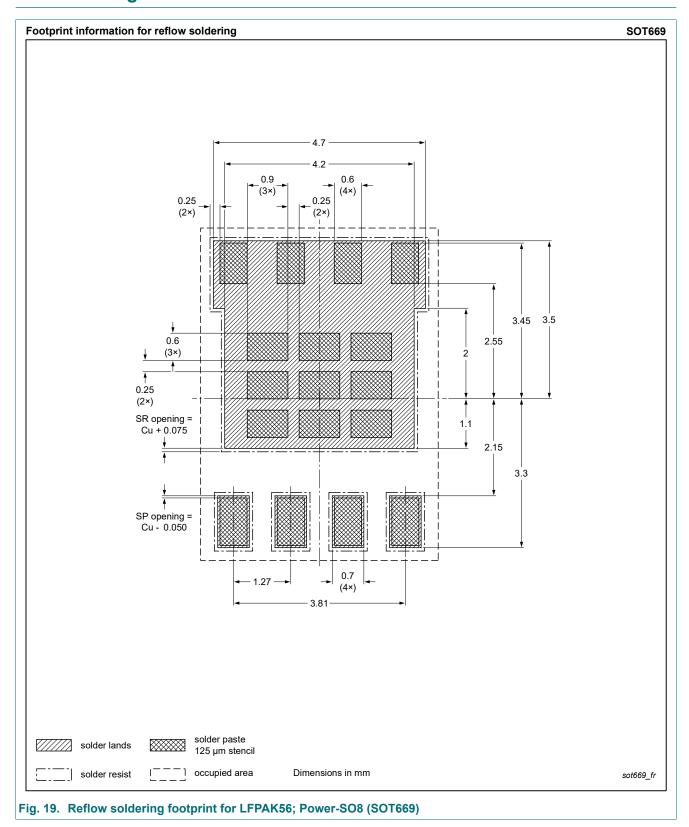


Fig. 17. Reverse recovery timing definition

11. Package outline



12. Soldering



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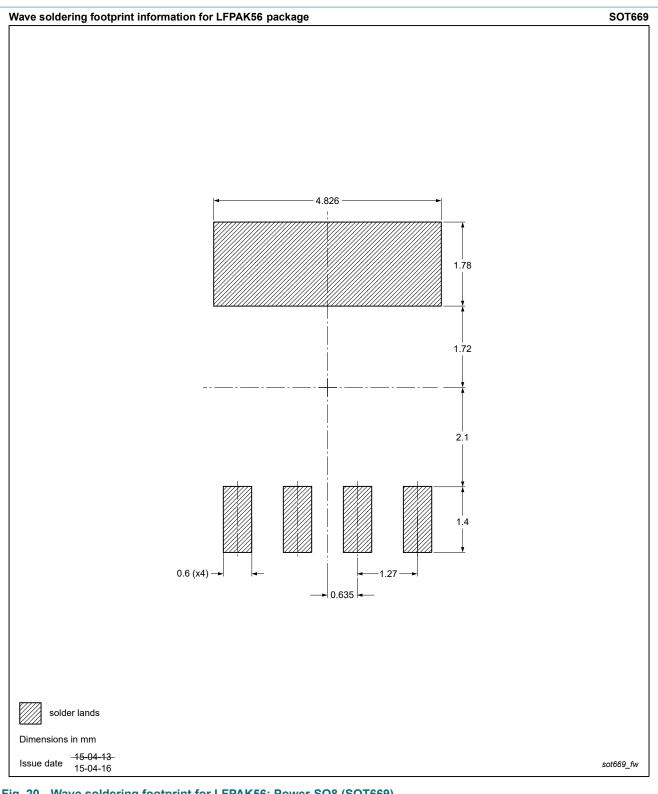


Fig. 20. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

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Document status [1][2]	Product status [3]	Definition
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